

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D T _A = +25°C
-60V	250mΩ @ V _{GS} = -10V	-2.1A
	300mΩ @ V _{GS} = -4.5V	-1.9A

Description

This MOSFET has been designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- DC-DC Converters
- Power Management Functions
- Uninterrupted Power Supply

Features and Benefits

- Low Gate Drive
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

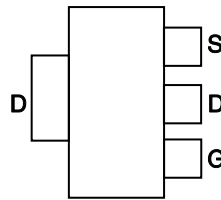
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish - Matte Tin Annealed over Copper Lead Frame. Solderable per MIL-STD-202, Method 208
- Weight: 0.112 grams (Approximate)

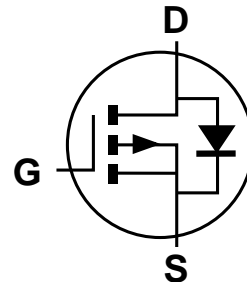
SOT223



Top View



Pin Out - Top View



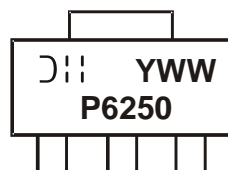
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Qualification	Case	Packaging
DMP6250SE-13	Standard	SOT223	2,500 / Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



= Manufacturer's Marking
 P6250 = Marking Code
 YWW = Date Code Marking
 Y or Y = Year (ex: 7 = 2017)
 WW = Week (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	-60	V
Gate-Source Voltage (Note 5)	V _{GS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = -10V	T _A = +25°C T _A = +70°C	-2.1 -1.7	A
	T _C = +25°C T _C = +70°C	-6.1 -4.9	A
Maximum Body Diode Continuous Current	I _S	-1.8	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	-11	A
Single Pulsed Avalanche Current (Note 7) L = 0.1mH	I _{AS}	-12	A
Single Pulsed Avalanche Energy (Note 7) L = 0.1mH	E _{AS}	8	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P _D	T _A = +25°C	1.8
		T _A = +70°C	1.1
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	69	°C/W
Total Power Dissipation (Note 6)	P _D	14	W
Thermal Resistance, Junction to Case (Note 6)	R _{θJC}	8.7	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-60	—	—	V	I _D = -250µA, V _{GS} = 0V
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	µA	V _{DS} = -60V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	-1	—	-3	V	V _{DS} = V _{GS} , I _D = -250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	128	250	mΩ	V _{GS} = -10V, I _D = -1.0A
			128	250		V _{GS} = -10V, I _D = -1.9A
			156	300		V _{GS} = -4.5V, I _D = -0.5A
			158	300		V _{GS} = -4.5V, I _D = -1.5A
Diode Forward Voltage	V _{SD}	—	—	-1.2	V	V _{GS} = 0V, I _S = -2.0A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{ISS}	—	551	—	pF	V _{DS} = -30V, V _{GS} = 0V f = 1MHz
Output Capacitance	C _{OSS}	—	25.7	—	pF	
Reverse Transfer Capacitance	C _{RSS}	—	19.1	—	pF	
Gate Resistance	R _g	—	12.1	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = -4.5V)	Q _g	—	4.8	—	nC	V _{DS} = -30V, I _D = -2A
Total Gate Charge (V _{GS} = -10V)	Q _g	—	9.7	—	nC	
Gate-Source Charge	Q _{gs}	—	1.5	—	nC	
Gate-Drain Charge	Q _{gd}	—	1.6	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	6.3	—	ns	V _{DS} = -30V, V _{GS} = -10V, R _G = 50Ω, I _D = -1A
Turn-On Rise Time	t _R	—	10.3	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	91.4	—	ns	
Turn-Off Fall Time	t _F	—	39.8	—	ns	
Reverse Recovery Time	t _{RR}	—	9.2	—	ns	I _S = -1A, di/dt = 100A/µs
Reverse Recovery Charge	Q _R	—	3.9	—	nC	

- Notes:
- AEC-Q101 V_{GS} maximum is ±16V.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - For design aid only, not subject to production testing.

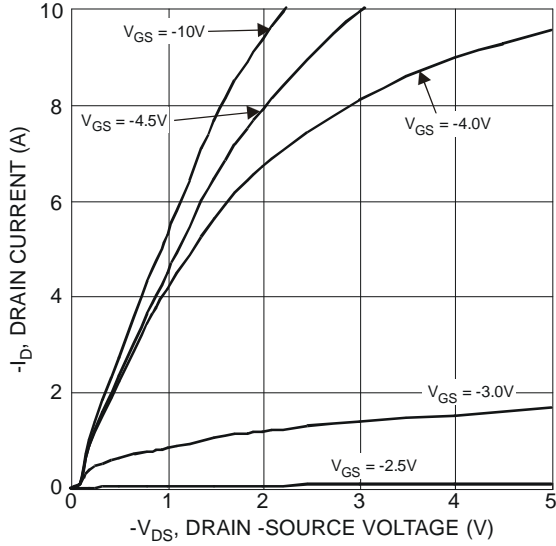


Figure 1 Typical Output Characteristics

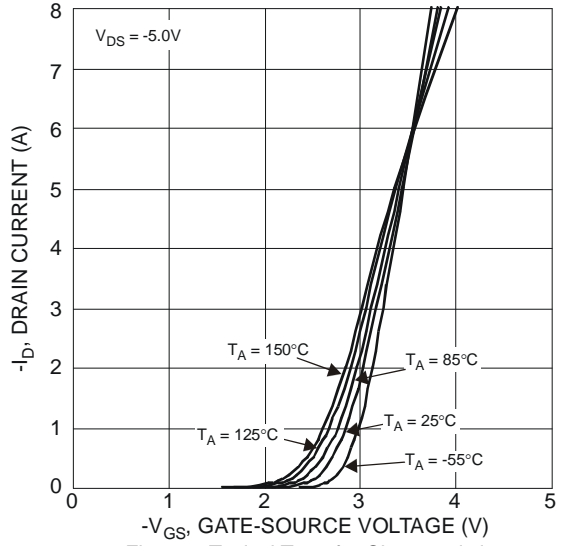


Figure 2 Typical Transfer Characteristics

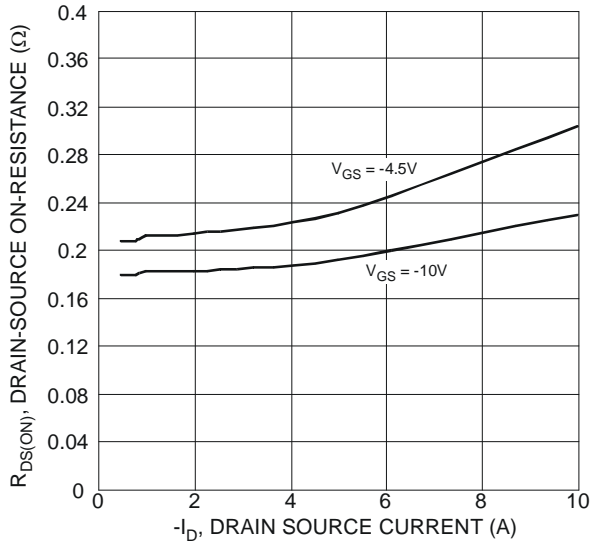


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

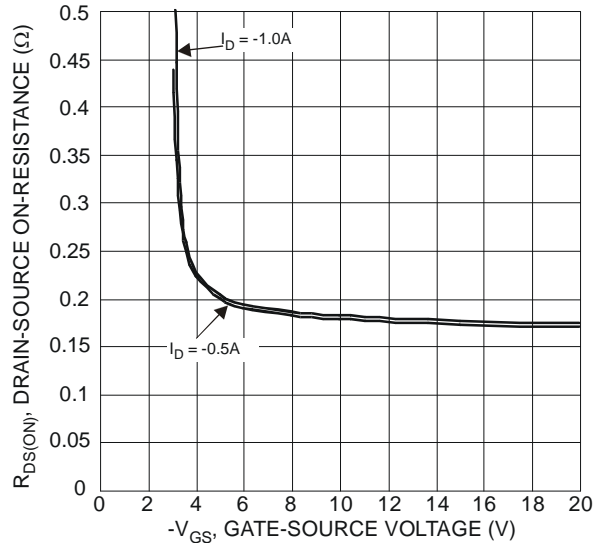


Figure 4 Typical Transfer Characteristics

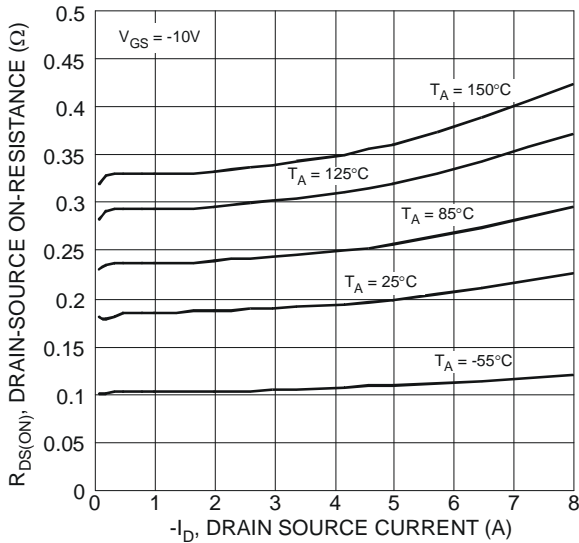


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

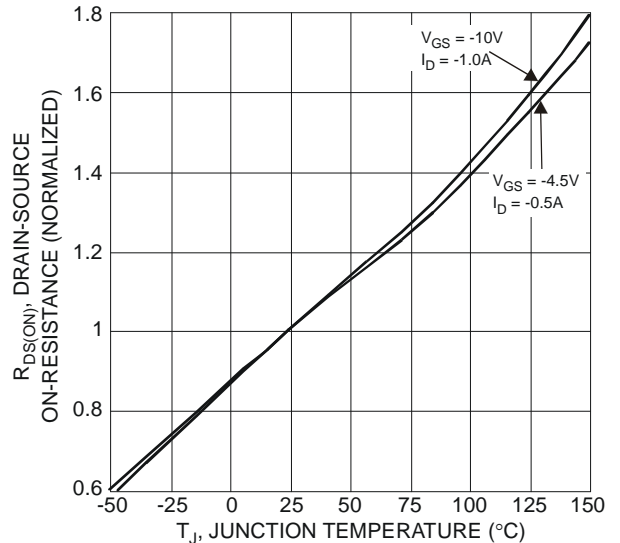


Figure 6 On-Resistance Variation with Temperature

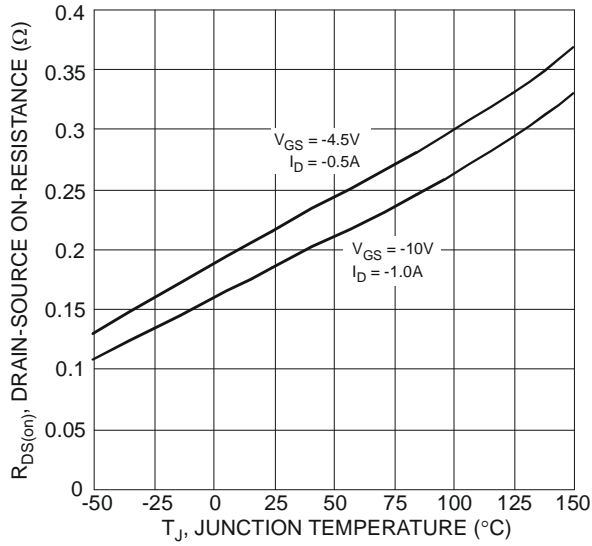


Figure 7 On-Resistance Variation with Temperature

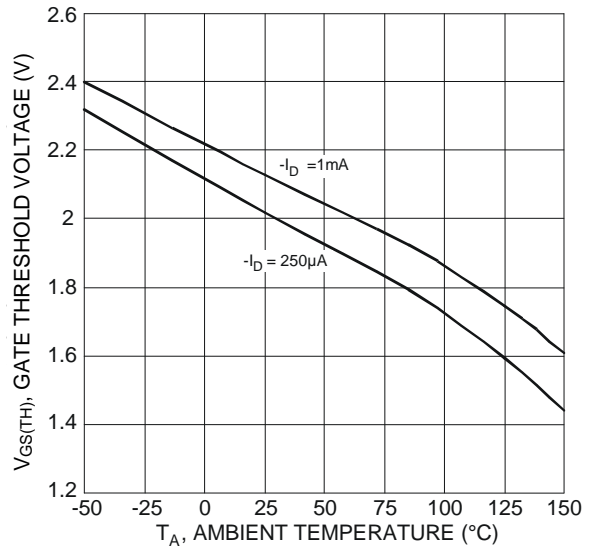


Figure 8 Gate Threshold Variation vs. Ambient Temperature

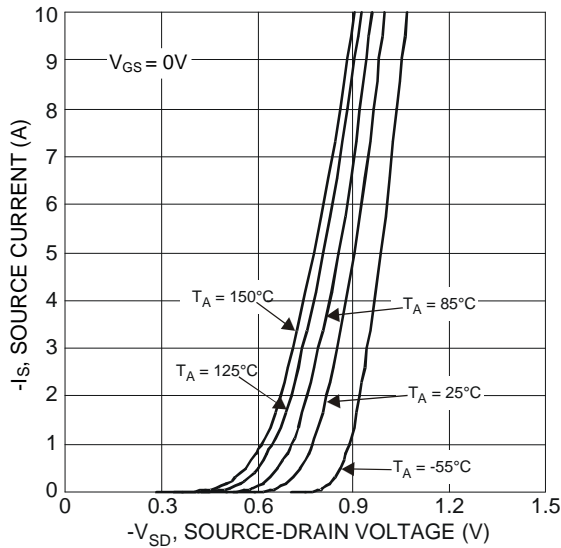


Figure 9 Diode Forward Voltage vs. Current

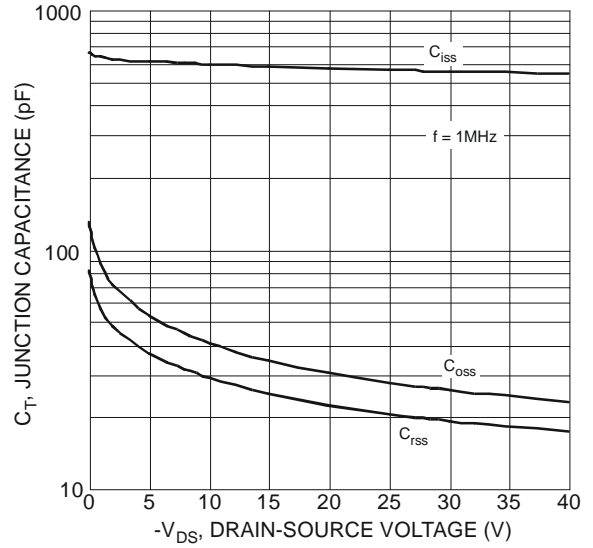


Figure 10 Typical Junction Capacitance

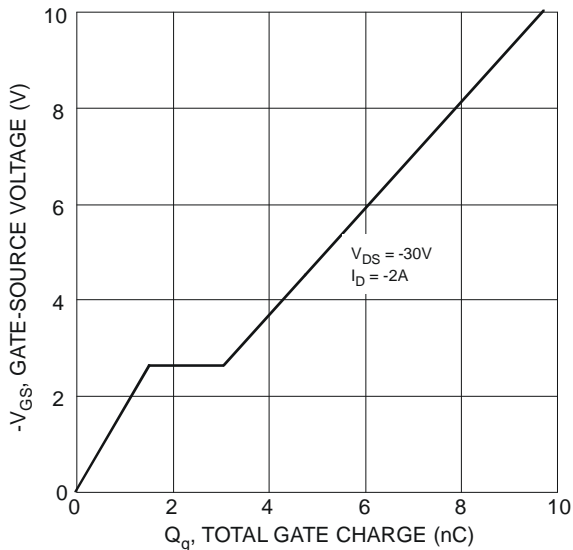


Figure 11 Gate-Charge Characteristics

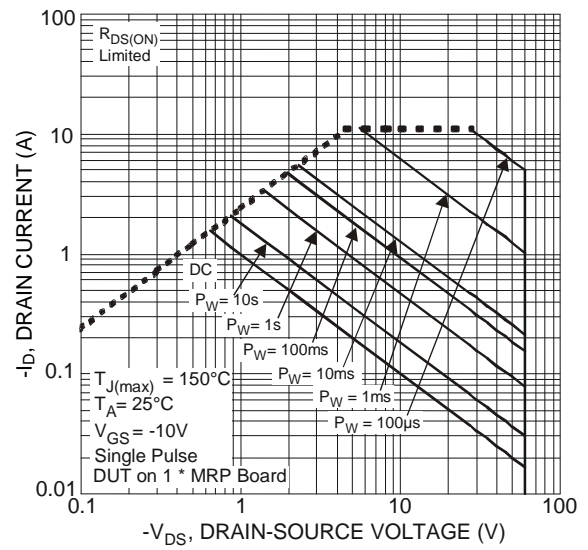


Figure 12 SOA, Safe Operation Area

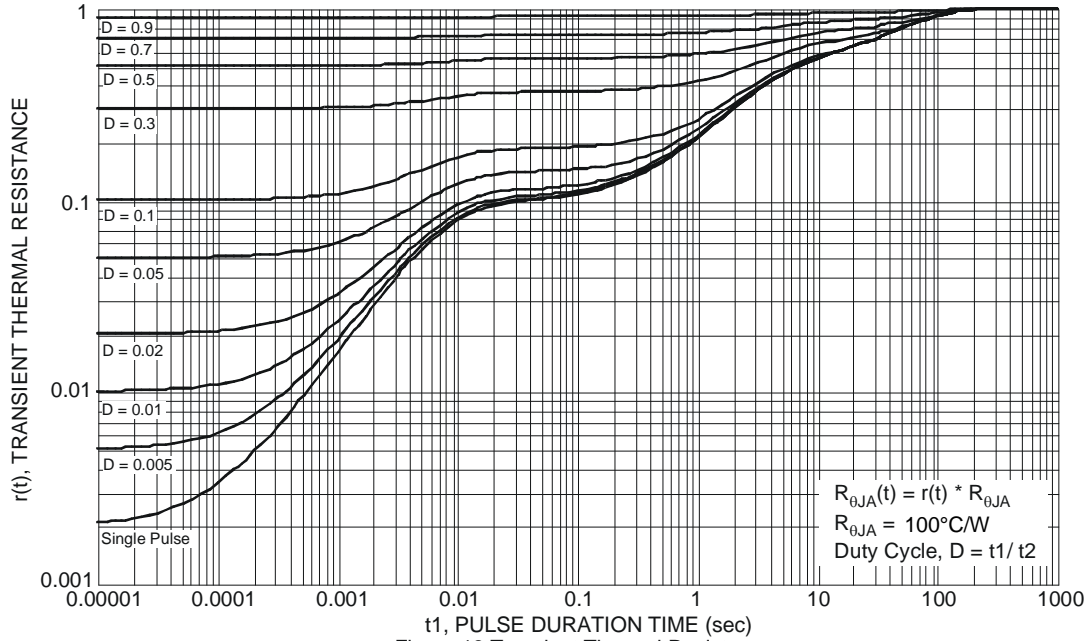
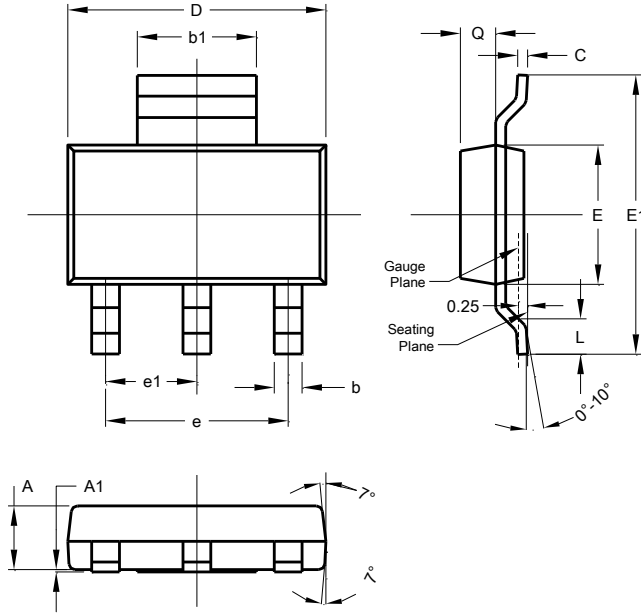


Figure 13 Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT223

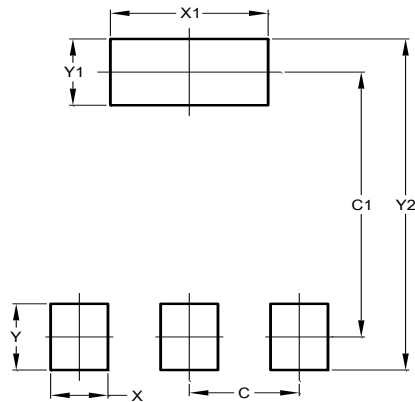


SOT223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b	0.60	0.80	0.70
b1	2.90	3.10	3.00
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	-	-	4.60
e1	-	-	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT223



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

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